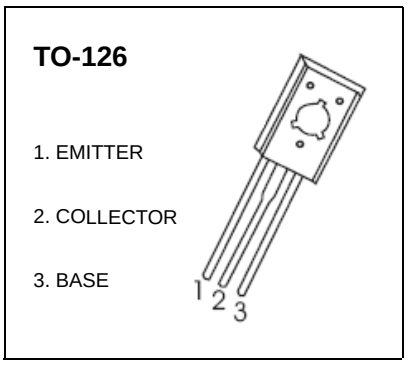
JIANGSU CHANGJING ELECTRONICS TECHNOLOGY CO., LTD

TO-126 Plastic-Encapsulate Transistors

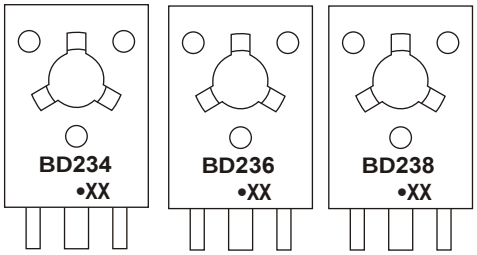
BD234 / BD236 / BD238 TRANSISTOR (PNP)



FEATURES

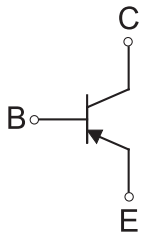
Complement to BD233/BD235/BD237 respectively

MARKING



BD234,BD236,BD238=Device code
Solid dot= Green molding compound device, if none, the normal device
XX=Code

Equivalent Circuit



ORDERING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
BD234	TO-126	Bulk	200pcs/Bag
BD236	TO-126	Bulk	200pcs/Bag
BD238	TO-126	Bulk	200pcs/Bag
BD234-TU	TO-126	Tube	60pcs/Tube
BD236-TU	TO-126	Tube	60pcs/Tube
BD238-TU	TO-126	Tube	60pcs/Tube

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

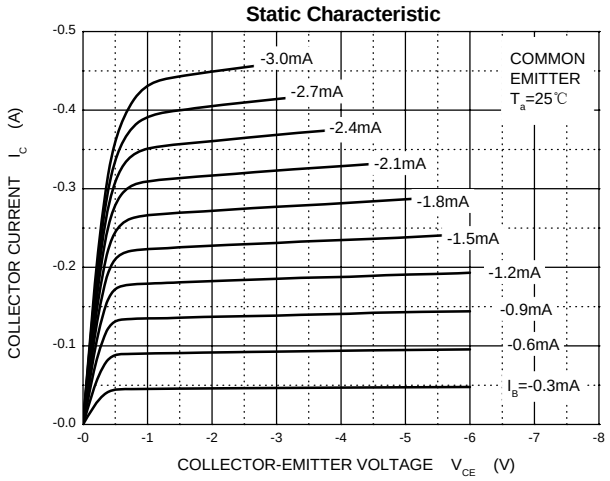
Symbol	Parameter		Value	Unit
V_{CBO}	Collector-Base Voltage	BD234	-45	V
		BD236	-60	
		BD238	-100	
V_{CEO}	Collector-Emitter Voltage	BD234	-45	V
		BD236	-60	
		BD238	-80	
V_{EBO}	Emitter-Base Voltage		-5	V
I_C	Collector Current –Continuous		-2	A
P_C	Collector Dissipation		1.25	W
P_C	Collector Dissipation (Tc=25℃)		25	W
$R_{\Theta JA}$	Thermal Resistance from Junction to Ambient		100	℃/W
$R_{\Theta JC}$	Thermal Resistance from Junction to Case		5	℃/W
T_J,T_{stg}	Operation Junction and Storage Temperature Range		-55~+150	℃

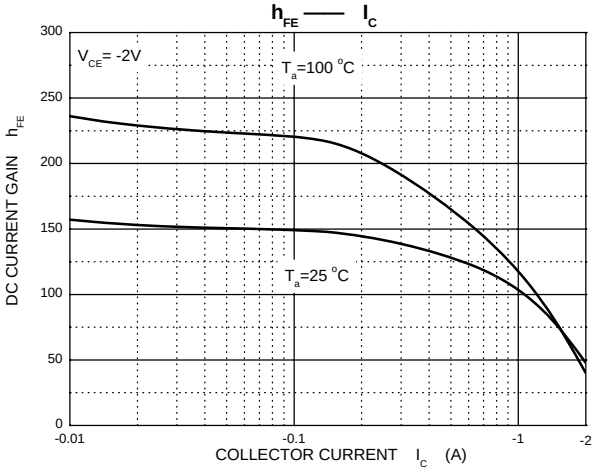
ELECTRICAL CHARACTERISTICS

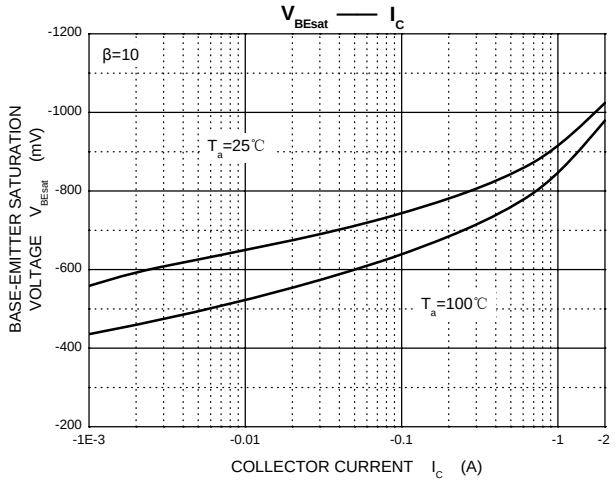
T_a=25℃ unless otherwise specified

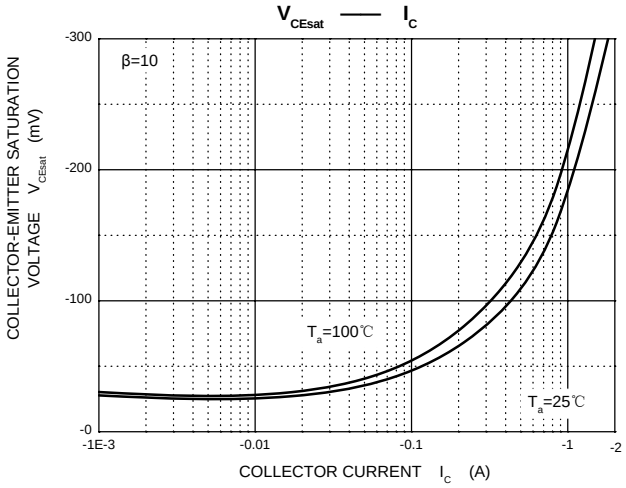
Parameter		Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	**BD234**	$V_{(BR)CBO}$	I_C=-1mA,I_E=0	-45		V
	BD236			-60		
	BD238			-100		
Collector-emitter breakdown voltage	**BD234**	$V_{(BR)CEO}$	I_C=-100mA,I_B=0	-45		V
	BD236			-60		
	BD238			-80		
Emitter-base breakdown voltage		$V_{(BR)EBO}$	I_E=-1mA,I_C=0	-5		V
Collector cut-off current	**BD234**	I_{CBO}	V_{CB}=-45V, I_E=0		-100	μA
	BD236		V_{CB}=-60V, I_E=0			
	BD238		V_{CB}=-100V, I_E=0			
Emitter cut-off current		I_{EBO}	V_{EB}=-5V, I_C=0		-1	mA
DC current gain		$h_{FE(1)}$	V_{CE}=-2V, I_C=-150mA	40		
		$h_{FE(2)}$	V_{CE}=-2V, I_C=-1A	25		
Collector-emitter saturation voltage		$V_{CE(sat)}$	I_C=-1A, I_B=-100m A		-0.6	V
Transition frequency		f_T	V_{CE}=-10V, I_C=-250mA, f =10MHz	3		MHz

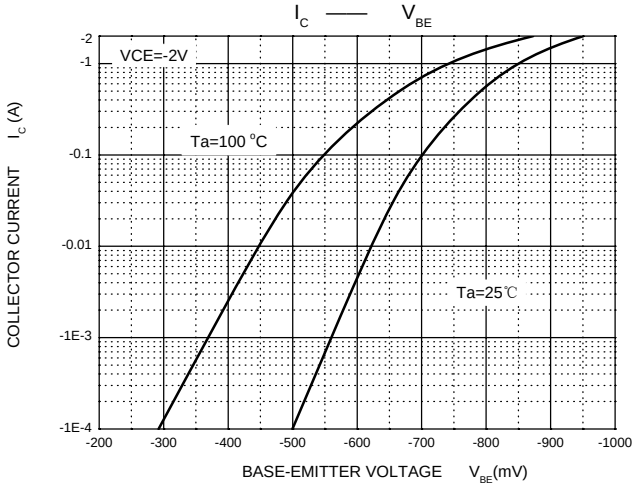
Typical Characteristics

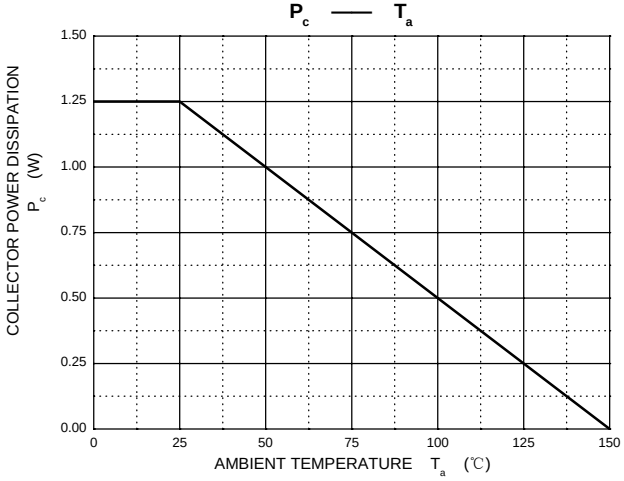




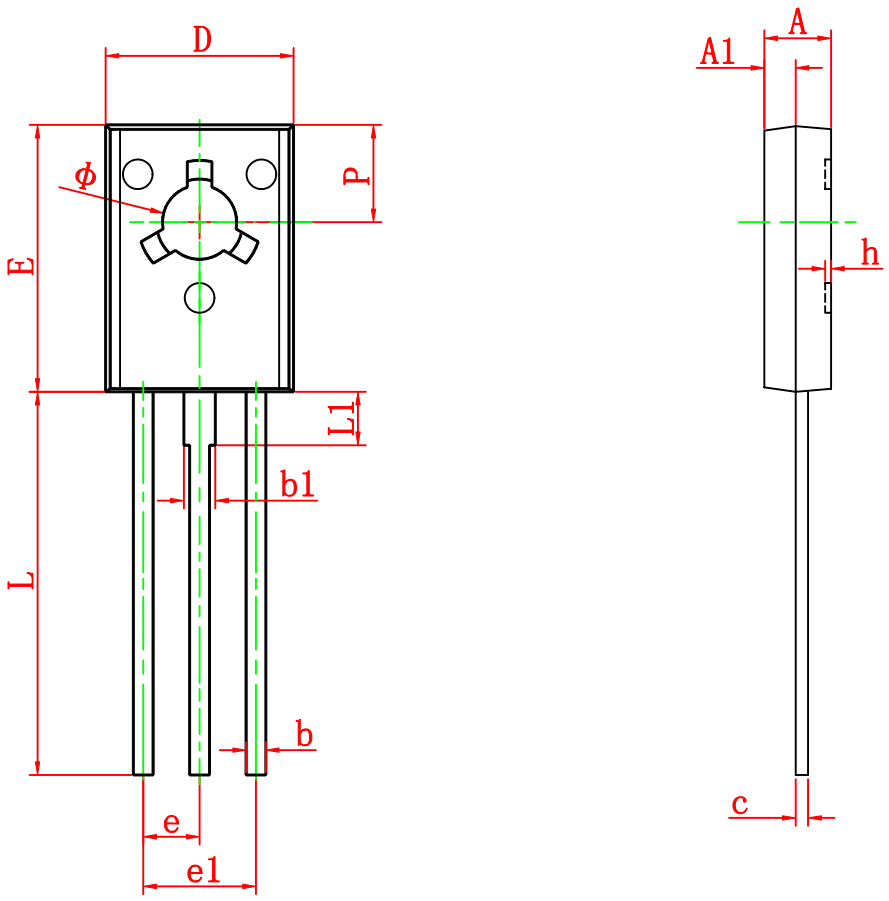








TO-126 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	2.500	2.900	0.098	0.114
A1	1.100	1.500	0.043	0.059
b	0.660	0.860	0.026	0.034
b1	1.170	1.370	0.046	0.054
c	0.450	0.600	0.018	0.024
D	7.400	7.800	0.291	0.307
E	10.600	11.000	0.417	0.433
e	2.290 TYP		0.090 TYP	
e1	4.480	4.680	0.176	0.184
h	0.000	0.300	0.000	0.012
L	15.300	15.700	0.602	0.618
L1	2.100	2.300	0.083	0.091
P	3.900	4.100	0.154	0.161
Φ	3.000	3.200	0.118	0.126

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